

Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 241998US2S		SERIAL NO. 10/649, New Application 704		
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Yoshiaki FUKUZUMI				
				FILING DATE Herewith		GROUP 2818		
U.S. PATENT DOCUMENTS								
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
	AA	S						
	AB							
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	AD							
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	AN							
FOREIGN PATENT DOCUMENTS								
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO			
	AO	S						
	AP							
	AQ							
	AR							
	AS							
	AT							
	AU							
	AV							
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)								
TH	AW	Roy SCHEUERLEIN, et al., "A 10ns Read and Write Non-Volatile Memory Array Using a Magnetic Tunnel Junction and FET Switch in each Cell", 2000 IEEE International Solid-State Circuits Conference, Digest of Technical Papers, pgs. 128-129						
TH	AX	Masashige SATO, et al., "Spin-Valve-Like Properties of Ferromagnetic Tunnel Junctions", Jpn. J. Appl. Phys. Vol. 36 (1997) pp. L200-L201						
	AY							
	AZ					<input type="checkbox"/> Additional References sheet(s) attached		
Examiner TH-TH-10					Date Considered Sept 2004			
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.								